

BUK6217-55C

N-channel TrenchMOS intermediate level FET Rev. 3 — 9 July 2012

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 1	-	-	44	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	80	W
Static char	acteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	16	19	mΩ
Dynamic c	haracteristics					
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	-	11.2	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 44 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	45	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			DPAK (SOT428)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6217-55C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK6217-55C	BUK6217-55C

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{GS}	gate-source voltage	DC	[1]	-16	16	V
		Pulsed	[2]	-20	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$		-	44	Α
		$T_{mb} = 100 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{}$		-	31	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3		-	175	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	80	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	ain diode					
Is	source current	T _{mb} = 25 °C		-	44	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	175	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 44 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	45	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy		[3][4][5]	-	-	J

^{[1] -16}V accumulated duration not to exceed 168 hrs

^[2] Accumulated pulse duration not to exceed 5mins.

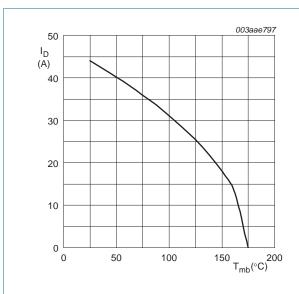
^[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[4] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[5] Refer to application note AN10273 for further information.

BUK6217-55C Nexperia

N-channel TrenchMOS intermediate level FET

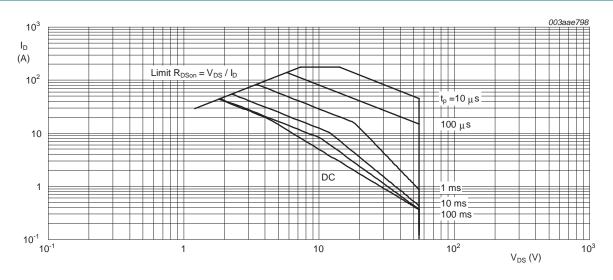


120 80 40 0 150 200 T_{mb} (°C) 100

 $P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$

Continuous drain current as a function of mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



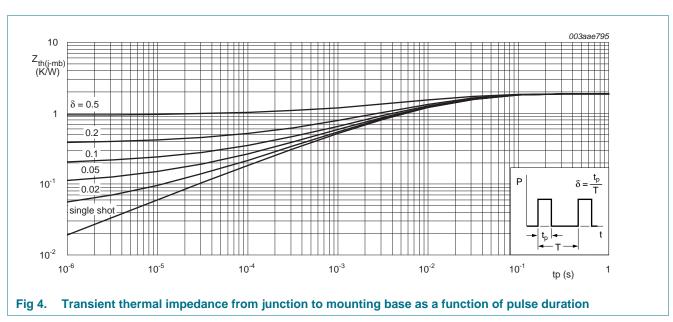
 T_{mb} = 25 °C; I_{DM} is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.87	K/W



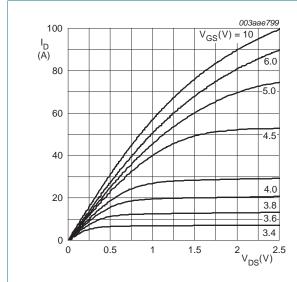
7. Characteristics

Table 7 Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	55	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	3.3	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see <u>Figure 10</u>	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C}; \text{see}$ Figure 11	-	16	19	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C};$ see Figure 11	-	19.6	24.5	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 12 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11	-	21.2	28.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 12; see Figure 11	-	-	42	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 44 \text{ V}$; $V_{GS} = 5 \text{ V}$; see Figure 13; see Figure 14	-	19.3	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$	-	33.8	-	nC
Q _{GS}	gate-source charge	see Figure 13; see Figure 14	-	5.2	-	nC
Q_{GD}	gate-drain charge		-	11.2	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1453	1950	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	156	190	pF
C _{rss}	reverse transfer capacitance		-	110	152	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$	-	9.8	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	29.7	-	ns
t _{d(off)}	turn-off delay time		-	56	-	ns
t _f	fall time		-	45.6	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	3.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 16	-	0.9	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	43	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}$	-	70	-	nC



 $T_j = 25$ °C; $t_p = 300 \,\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

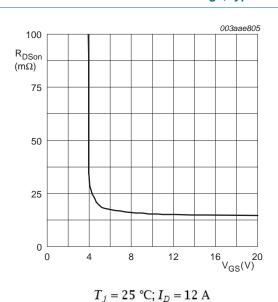
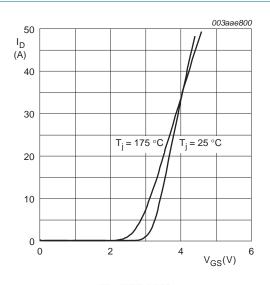
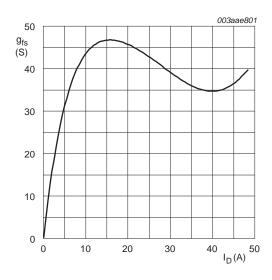


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



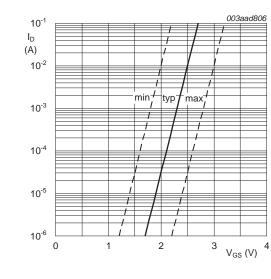
$$V_{DS} > I_D \times R_{DSon}$$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}\text{C}; \ V_{DS} = 25 \,^{\circ}\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 9. Sub-threshold drain current as a function of gate-source voltage

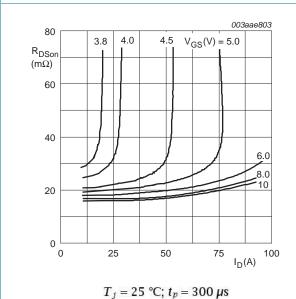
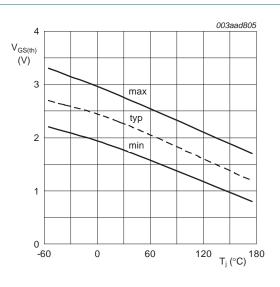


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



$$I_D = 1mA; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature

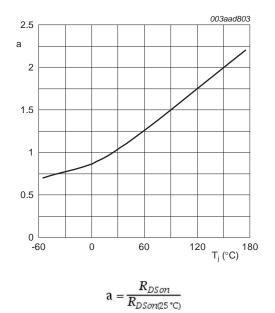
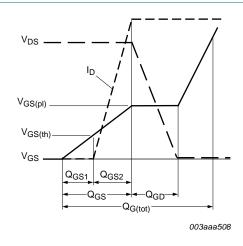


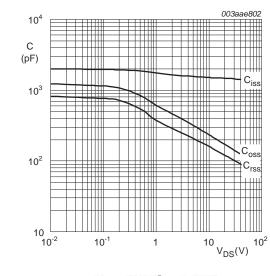
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



 $T_j = 25$ °C; $I_D = 25$ A

Fig 13. Gate charge waveform definitions

Fig 14. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

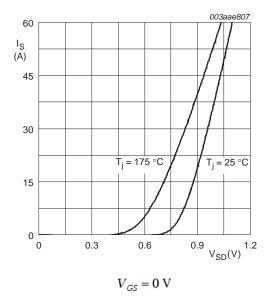


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

8. Package outline

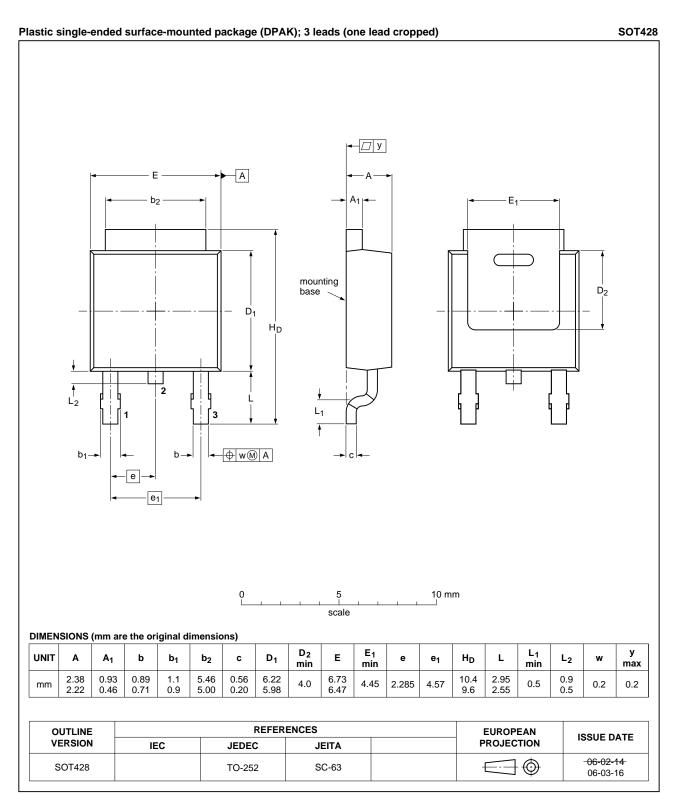


Fig 17. DPAK (SOT428)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6217-55C v.3	20120709	Product data sheet	-	BUK6217-55C v.2
Modifications:	 Various changes 	to content.		
BUK6217-55C v.2	20101004	Product data sheet	-	BUK6217-55C v.1

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10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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BUK6217-55C

N-channel TrenchMOS intermediate level FET

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